



PART B — (5 × 16 = 80 marks)

11. (a) (i) Compare brittle fracture with ductile fracture. (4)  
(ii) Outline Griffith's theory of brittle fracture and obtain an expression for fracture stress. (12)

Or

- (b) (i) Explain edge dislocation. (4)  
(ii) Outline any three methods of improving mechanical properties. (12)
12. (a) (i) Explain the variation of Fermi level with temperature and impurity concentration in a n-type semiconductor. (8)  
(ii) Explain any two applications of Hall effect. (8)

Or

- (b) (i) Write down an expression for the intrinsic carrier concentration. Explain electrical conduction in an intrinsic material. (8)  
(ii) Outline a method of determining the band-gap of a semiconductor. (8)
13. (a) (i) Explain electronic and ionic polarisations. (10)  
(ii) Explain dielectric loss. (6)

Or

- (b) (i) What are Ferromagnetic domains? Explain magnetic hysteresis on the basis of Ferromagnetic domains. (10)  
(ii) Write a note on magnetic bubble memories. (6)
14. (a) (i) Derive Einstein's mass-energy relation. (10)  
(ii) Explain the term binding energy. (6)

Or

- (b) (i) Explain the salient features of a nuclear power station. (10)  
(ii) Write a note on nuclear fusion. (6)
15. (a) (i) Distinguish between Type I and Type II superconductors. (8)  
(ii) Write a note on High  $T_c$  superconductors. (8)

Or

- (b) (i) Explain the characteristic features and applications of metallic glasses. (12)  
(ii) What are shape memory alloys? (4)